

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
29 October 2009 (29.10.2009)

PCT

(10) International Publication Number
WO 2009/130050 A1

(51) International Patent Classification:
G01N 1/32 (2006.01)

(21) International Application Number:
PCT/EP2009/003028

(22) International Filing Date:
24 April 2009 (24.04.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
08290398.0 25 April 2008 (25.04.2008) EP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: ETCHING COMPOSITION, IN PARTICULAR FOR STRAINED OR STRESSED SILICON MATERIALS, METHOD FOR CHARACTERIZING DEFECTS ON SURFACES OF SUCH MATERIALS AND PROCESS OF TREATING SUCH SURFACES WITH THE ETCHING COMPOSITION

(57) Abstract: The present invention provides a chromium-free etching composition suitable for treating various silicon-containing surfaces, including strained silicon on insulator surfaces as well as stressed silicon surfaces. The novel and inventive etching composition in accordance with the present invention comprises hydrofluoric acid, nitric acid, acetic acid and an alkali iodide, preferably potassium iodide.



WO 2009/130050 A1